

Rev.A Jul.-2023

TO-252 N MOS

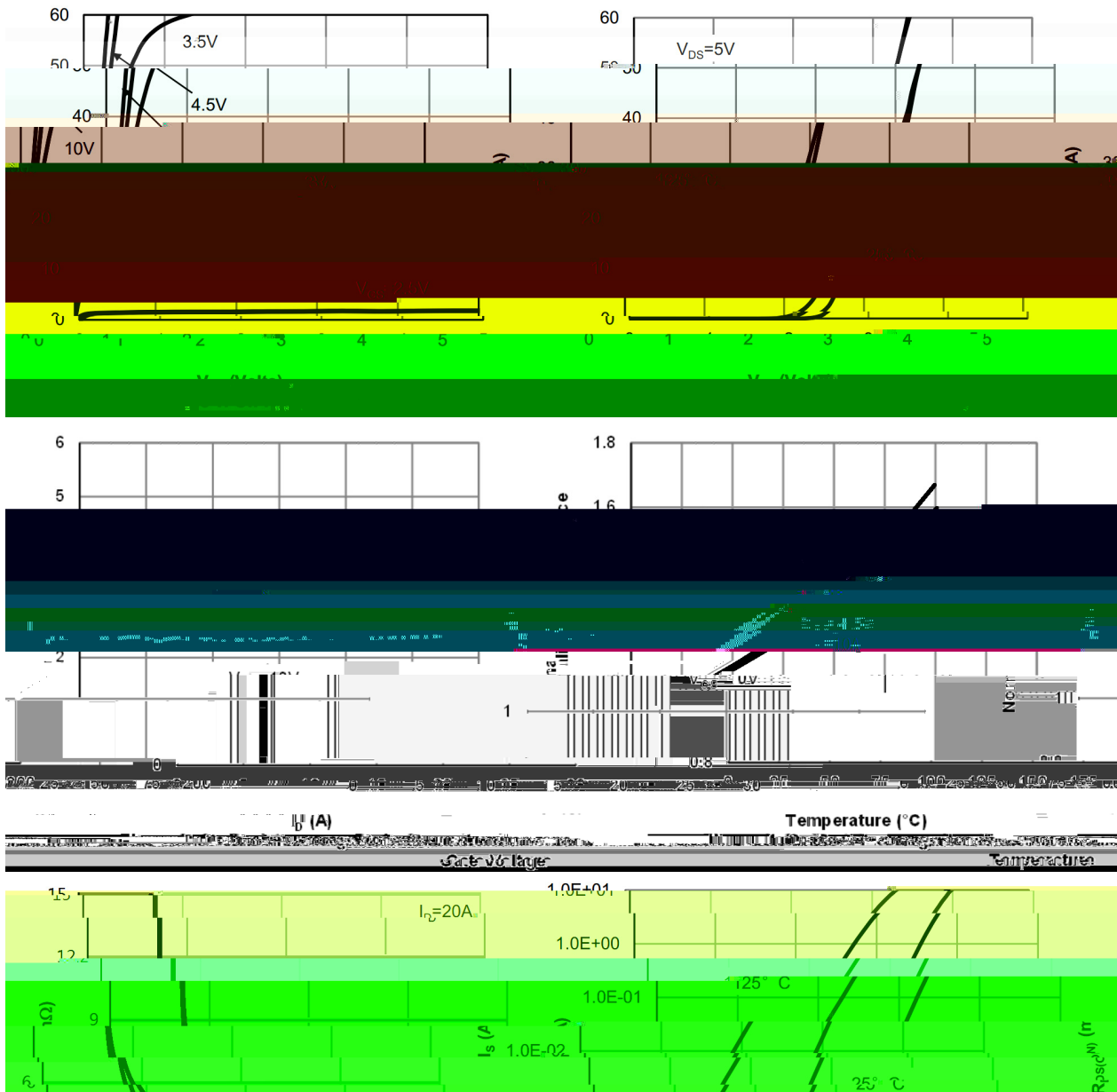
N-Channel Enhancement Mode Field Effect Transistor in a TO-252 Plastic Package.

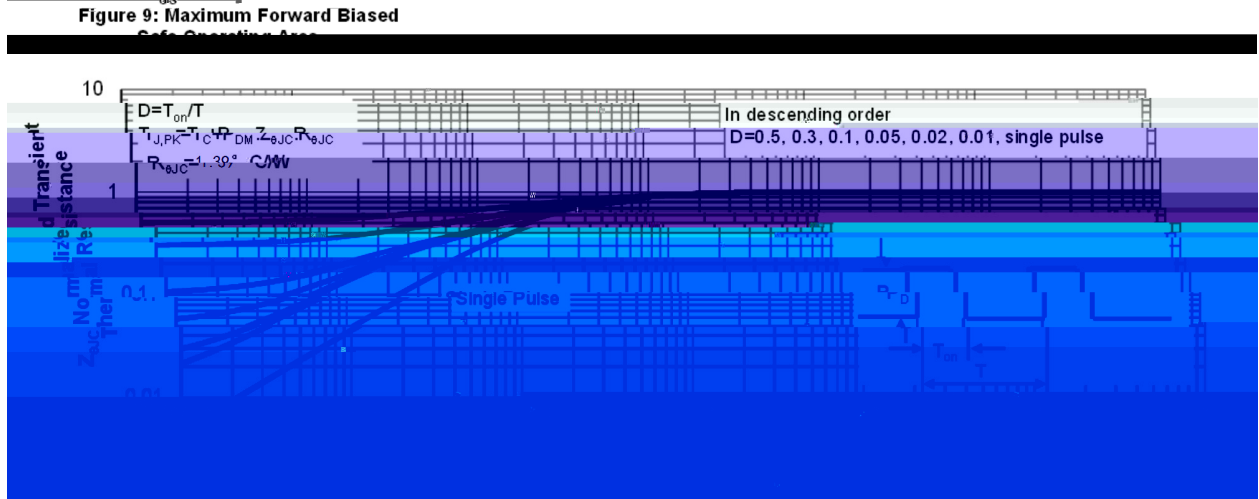
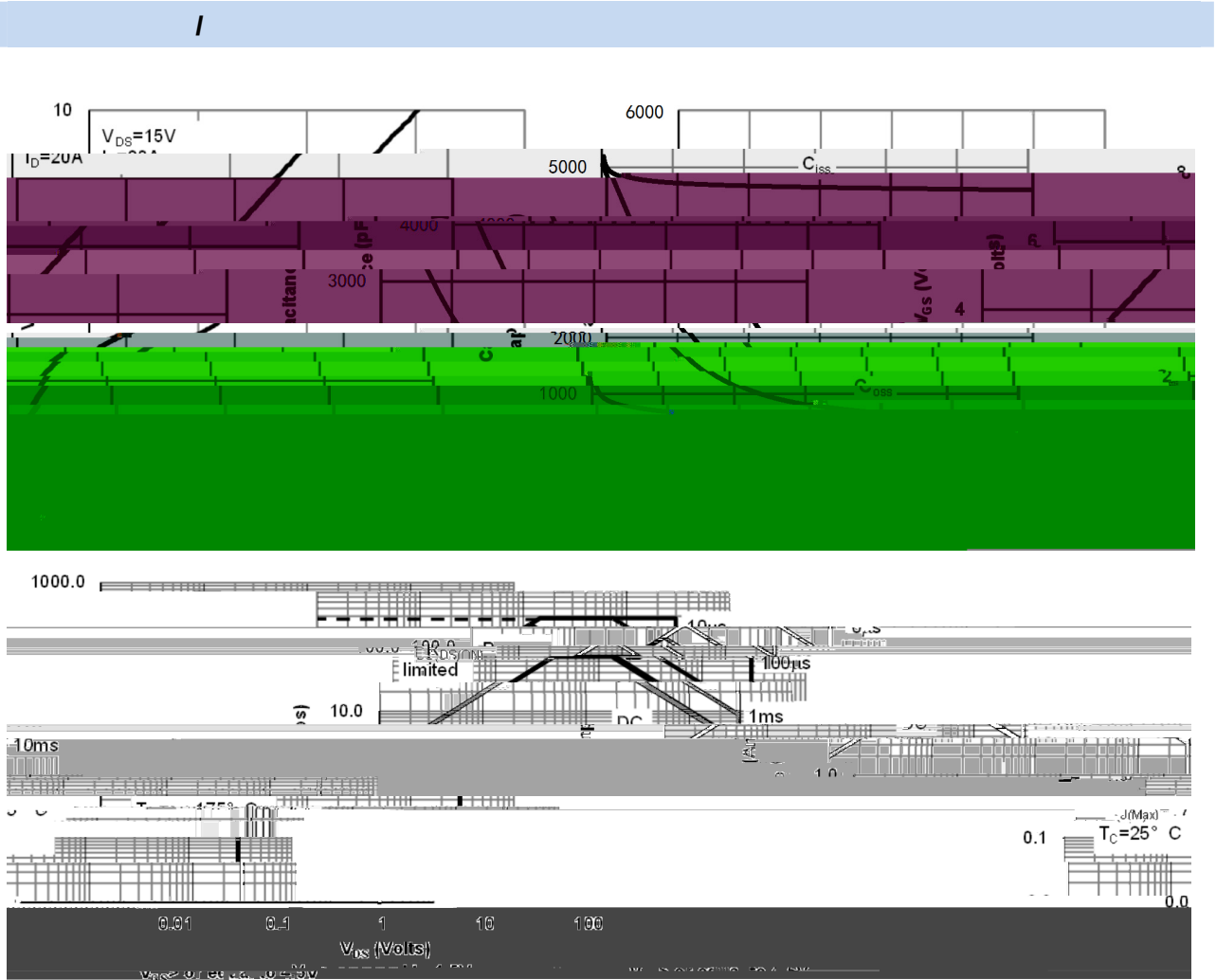
$V_{DS} (V) = 30V$ I

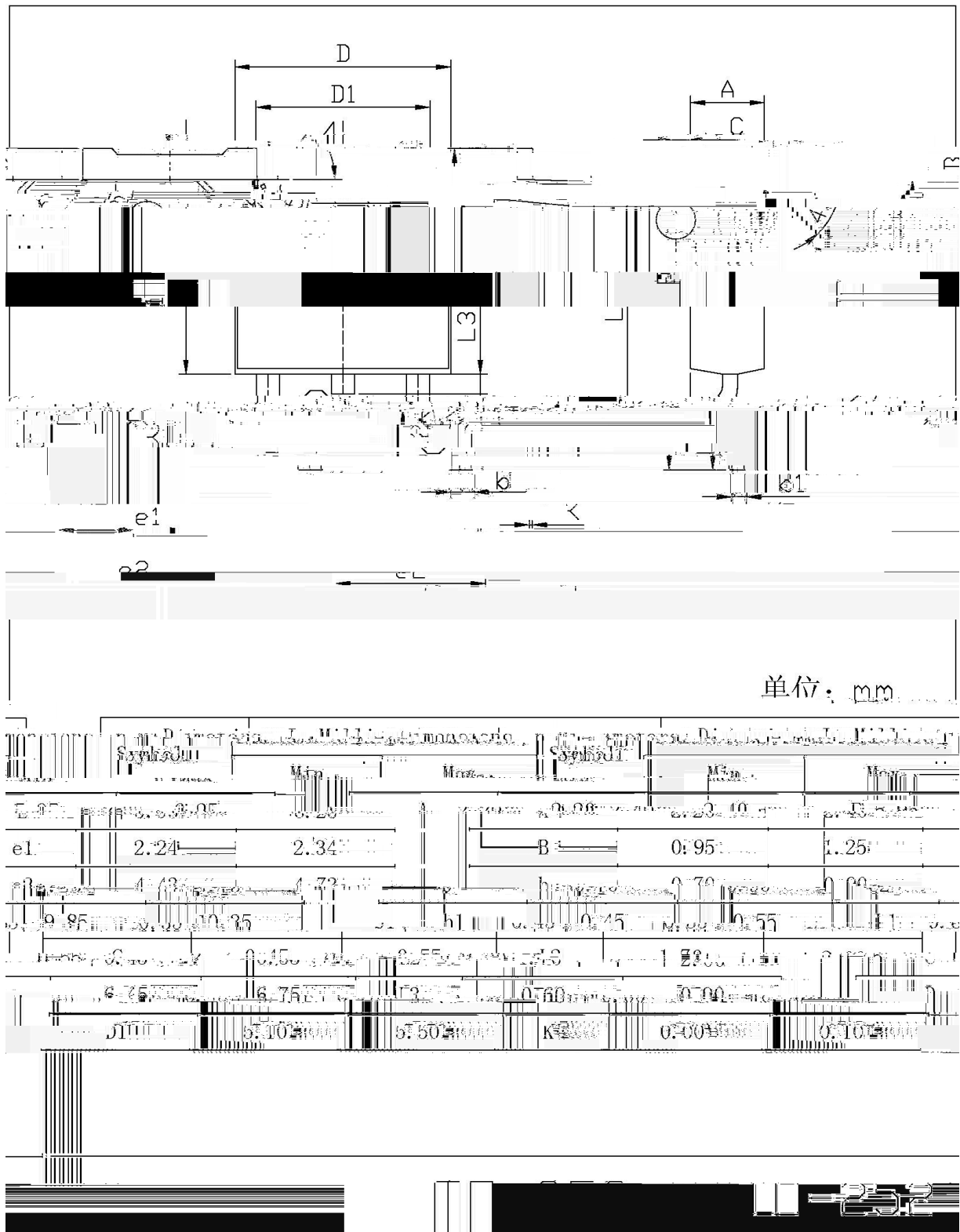
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Parameter

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V$ $V_{DS}=15V$ $I_D=20A$		32		nC
Total Gate Charge	$Q_{g(4.5V)}$			15		
Gate Source Charge	Q_{gs}			5.2		
Gate Drain Charge	Q_{gd}			6.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=15V$ $R_L=0.75\Omega$ $R_{GEN}=3\Omega$		8.5		ns
Turn-On Rise Time	t_r			4.2		
Turn-Off Delay Time	$t_{d(off)}$			30		
Turn-Off Fall Time	t_f			5.7		







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